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Attorney Docket No. CIS-001CP

N THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS:

Schowalter and Slack

SERIAL NO.:

10/822,336

GROUP NO.:

1722

FILING DATE:

April 12, 2004

EXAMINER:

Kunemund, R.

TITLE:

Powder Metallurgy Crucible For Aluminum Nitride Crystal Growth

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. References A11 and B1 were previously cited in U.S. Patent Application Serial No. 09/251,106, from which this application claims priority. Accordingly, pursuant to 37 C.F.R. § 1.98(d), Applicants have not supplied copies of those references, but shall do so upon request.

Also, in accordance with the U.S. Patent Office's partial waiver of the requirement under 37 C.F.R. 1.98(a)(2), Applicants have not supplied copies of the U.S. patents and publications cited in the attached Form PTO-1449, but shall do so upon request. Copies of the foreign patent documents B2 and non-patent publications C1-C7 are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

	(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the						
		merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or						
	(2)	after the period defined in (1) but before the mailing date of a final action or a notic of allowance under 37 C.F.R. 1.311, and						
		the requisite Statement is below, OR						
		the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or						
	(3)	after the mailing date of a final action or notice of allowance but before the payment of the issue fee, AND						
		the requisite Statement is below, AND						
		the requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein.						
It is r	espectf	fully requested that each of the patents and publications listed on the attached Form						
PTO-1449	, and ot	her information contained herein, be made of record in this application.						
		Respectfully submitted,						
		Im						
Date: Janu	uary 13	. 2006						
Reg. No. 5	•	Mark L/Beloborodov						
		Attorney for Applicant(s)						
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Tel. No.: (•	The state of the s						
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SHEET 1 OF 2

ATTORNEY DOCKET NO.: CIS-001CP

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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							GROUP:			1722		
				U.S	S. PATEN	1T	DOCUM	ENTS				
EXAM INIT.		DOCUMENT NU	DATE		NAME		CLASS	SUB CLASS	l	NG DATE II ROPRIATE		
	A1	4,234,554		11/1	8/80	Ra	abenau et al	•				
	A2 5,858,085 01/12/1999 A3 5,858,086 01/12/1999 A4 5,909,036 06/01/1999		2/1999	Aı	rai <i>et al</i> .							
			2/1999	Н	unter							
			06/0	06/01/1999		ınaka <i>et al</i> .						
	A5	5,972,109	2,109		10/26/1999		unter					
	A6	6,001,748		06/04/1997		Ta	naka <i>et al</i> .					
	A7	6,045,612		04/0	04/04/2000		unter					
	A8	6,048,813			04/11/2000 05/16/2000		unter					
	A9	6,063,185					unter					
	A10	6,086,672		07/1	/11/2000		unter					
	A11	6,187,089	02/13/2001		3/2001	Phillips et al.						
	All	6,296,956		10/0	0/02/2001		unter					
·			F	ORE	IGN PAT	ΓEΝ	NT DOCU	JMENTS	5			
EXAM. INIT.		DOCUMENT NUMBER	DATE		COUNTRY CODE		CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY		ENGLISH LANG (Y/N)
	Bl	2000-154090	06/200	00	JP					YES		N
	B2	02 018379A	01/22/1990		JP					YES		N
EXAMINER					DATE CONSIDERED							

FORM F	PTO - 1	1449	ATTORNEY DOCKET NO.: CIS-001CP					
		TAL INFORMATION	APPLICANTS:	Schowalter and Slack				
DISCLO	SURE	STATEMENT	SERIAL NO.:	10/822,336				
			FILING DATE:	April 12, 2004				
			GROUP:	1722				
		OTHER ART, JOUR	NAL ARTICLES, ETC.					
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
	C1	Dryburgh, "Estimation of maximum growth Crystal Growth 125, 65-68 (1992).	imation of maximum growth rate for aluminum nitride crystals by direct sublimation", J. 125, 65-68 (1992).					
	C2	A.S. Segal S. Yu, Karpov, Yu. N. Makarov, E.N. Mokhov, A.D. Roenkov, M.G. Ramm, Yu. A. Vodakov, "On mechanisms of sublimination growth of AIN bulk crystals", <i>J. Crystal Growth</i> 211, 68-72 (2000).						
	C3	 B. Raghothamachar, W.M. Vetter, M. Dudley, R. Dalmau, R. Schlesser, Z. Sitar, E. Michaels, and J.W. Kolis, "Synchrotron white beam topography characterization of physical vapor transport grown A1N and ammonothermal GaN", J. Crystal Growth 246, 271-280 (2002). R. Schlesser, R. Dalmau, and Z. Sitar, "Seeded growth of A1N bulk single crystals by sublimation", J. Crystal Growth 241, 416-420 (2002). L.J. Schowalter, G.A. Slack, J.B. Whitlock, K. Morgan, S.B. Schujman, B. Raghothamachar, M. Dudley, and K.R. Evans, "Fabrication of native, single-crystal AIN substrates", Phys. Stat. Sol. (c), 104, (2003). V. Noveski, R. Schlesser, S. Mahajan, S. Beaudoin, and Z. Sitar, "Growth of A1N crystals on A1N/SiC seeds by A1N powder sublimation in nitrogen atmostphere", MRS Internet J. Nitride Semicond. Res. 9, 2 (2004). 						
	C4							
	C5							
	C6							
	C7	C7 V. Noveski, R. Schlesser, S. Mahajan, S. Beaudoin, and Z. Sitar, "Mass transfer in A1N crystal growth at high temperatures", <i>J. Crystal Growth</i> 264, 369-378 (2004).						
EXAMIN	ER		DATE CONSIDERED					

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